N-Channel 75-V (D-S) 200°C MOSFET

CHARACTERISTICS

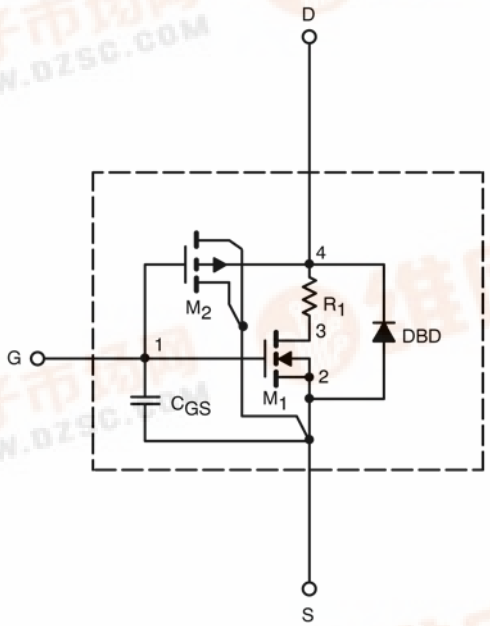
- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the –55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the –55 to 125°C temperature ranges under the pulsed 0 to 10V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

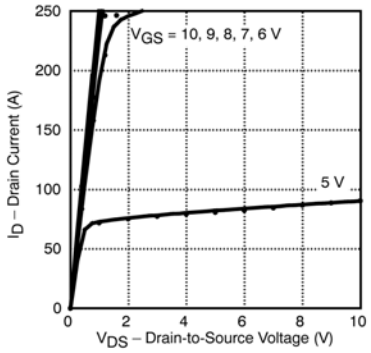
SUBCIRCUIT MODEL SCHEMATIC

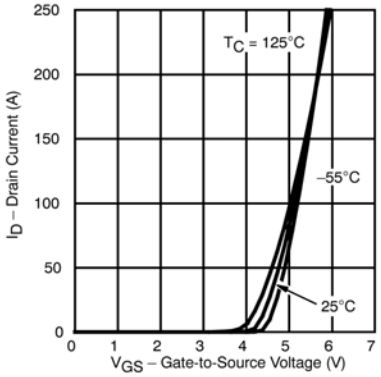


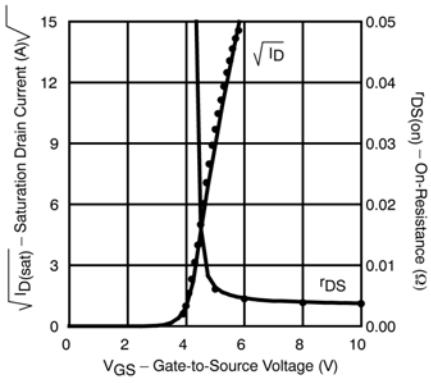
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)					
Parameter	**Symbol**	**Test Conditions**	**Simulated Data**	**Measured Data**	**Unit**
Static					
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	3.1		V
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} > 5 V, V_{GS} = 10 V	1197		A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A	0.0038	0.0038	Ω
		V_{GS} = 10 V, I_D = 30 A, T_J = 125°C	0.0063		
		V_{GS} = 10 V, I_D = 30 A, T_J = 200°C	0.0084		
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 30 A	109		S
Forward Voltage[a]	V_{SD}	I_S = 110 A, V_{GS} = 0 V	0.92	1	V
Dynamic[b]					
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	7663	7900	Pf
Output Capacitance	C_{oss}		936	950	
Reverse Transfer Capacitance	C_{rss}		406	550	
Total Gate Charge[c]	Q_g	V_{DS} = 35 V, V_{GS} = 10 V, I_D = 110 A	139	145	NC
Gate-Source Charge[c]	Q_{gs}		36	30	
Gate-Drain Charge[c]	Q_{gd}		45	45	
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 35 V, R_L = 0.40 Ω I_D ≅ 110 A, V_{GEN} = 10 V, R_G = 2.5 Ω	88	25	Ns
Rise Time[c]	t_r		110	200	
Turn-Off Delay Time[c]	$t_{d(off)}$		130	65	
Fall Time[c]	t_f		149	165	
Reverse Recovery Time	t_{rr}	I_F = 85 A, di/dt = 100 A/µs	55	80	

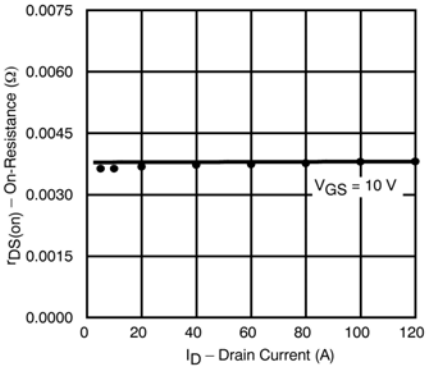
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

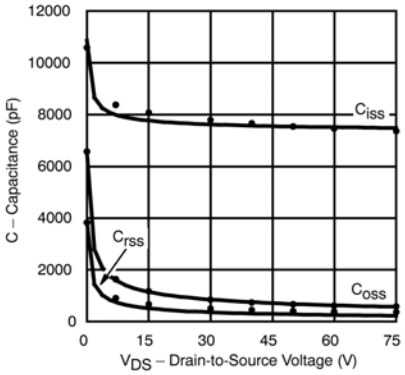
COMPARISON OF MODEL WITH MEASURED DATA (T_J=25°C UNLESS OTHERWISE NOTED)

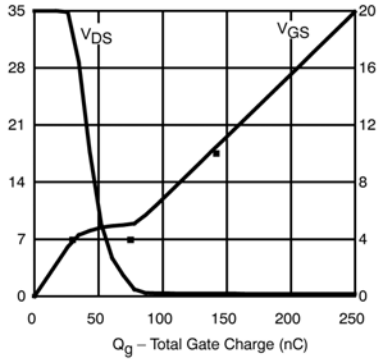












Note: Dots and squares represent measured data.